PRELIMINARY PRODUCT SPECIFICATION

SHARP

Integrated Circuits Group

LH28F128BFHT-PBTL75A

Flash Memory
16Mbit (8Mbitx16)

(Model Number: LHF12F17)

Spec. Issue Date: June 7, 2004

SHARP

SPEC No.	FM046012
ISSUE:	Jun. 7, 2004

To; _____

PRELIMINARY

SPECIFICATIONS

Product Type 128Mbit Flash Memory

LH28F128BFHT—PBTL75A

Model No. (LHF12F17)

This device specification is subject to change without notice.

* This specifications contains 32 pages including the cover and appendix.

CUSTOMERS ACCEPTANCE

DATE: _____

BY: _____

PRESENTED

BY: M. Nawaki

M. NAWAKI
Dept. General Manager

REVIEWED BY: R. Matsuyama

PREPARED BY: N. Inoue

Product Development Dept. II
System-Flash Division
Integrated Circuits Group
SHARP CORPORATION

- Handle this document carefully for it contains material protected by international copyright law. Any reproduction, full or in part, of this material is prohibited without the express written permission of the company.

- When using the products covered herein, please observe the conditions written herein and the precautions outlined in the following paragraphs. In no event shall the company be liable for any damages resulting from failure to strictly adhere to these conditions and precautions.

  (1) The products covered herein are designed and manufactured for the following application areas. When using the products covered herein for the equipment listed in Paragraph (2), even for the following application areas, be sure to observe the precautions given in Paragraph (2). Never use the products for the equipment listed in Paragraph (3).

  - Office electronics
  - Instrumentation and measuring equipment
  - Machine tools
  - Audiovisual equipment
  - Home appliance
  - Communication equipment other than for trunk lines

  (2) Those contemplating using the products covered herein for the following equipment which demands high reliability, should first contact a sales representative of the company and then accept responsibility for incorporating into the design fail-safe operation, redundancy, and other appropriate measures for ensuring reliability and safety of the equipment and the overall system.

  - Control and safety devices for airplanes, trains, automobiles, and other transportation equipment
  - Mainframe computers
  - Traffic control systems
  - Gas leak detectors and automatic cutoff devices
  - Rescue and security equipment
  - Other safety devices and safety equipment, etc.

  (3) Do not use the products covered herein for the following equipment which demands extremely high performance in terms of functionality, reliability, or accuracy.

  - Aerospace equipment
  - Communications equipment for trunk lines
  - Control equipment for the nuclear power industry
  - Medical equipment related to life support, etc.

  (4) Please direct all queries and comments regarding the interpretation of the above three Paragraphs to a sales representative of the company.

- Please direct all queries regarding the products covered herein to a sales representative of the company.

CONTENTS

LH28F128BFHT-PBTL75A
128Mbit (8Mbit×16)
Page Mode Dual Work Flash MEMORY

■ 128-M density with 16-bit I/O Interface

■ High Performance Reads
- 75/25ns 8-Word Page Mode

■ 6-Plane Dual Work Operation
- Read operations are available during Block Erase or (Page Buffer) Program between two different Planes
- Plane Architecture: 16M, 24M, 24M, 24M, 24M, 16M

■ Low Power Operation
- 2.7V Read and Write Operations
- V_{CCQ} for Input/Output Power Supply Isolation
- Automatic Power Savings Mode reduces I_{CCR} in Static Mode

■ Enhanced Code + Data Storage
- 5µs Typical Erase/Program Suspends

■ OTP (One Time Program) Block
- 4-Word Factory-Programmed Area
- 4-Word User-Programmable Area

■ High Performance Program with Page Buffer
- 16-Word Page Buffer
- 5µs/Word (Typ.) at WP#/ACC=9.5V

■ Operating Temperature -40°C to +85°C

■ CMOS Process (P-type silicon substrate)

■ Flexible Blocking Architecture
- Eight 4-Kword Parameter Blocks
- Two-hundred and fifty-five 32-Kword Main Blocks
- Bottom Parameter Location

■ Enhanced Data Protection Features
- Individual Block Lock and Block Lock-Down with Zero-Latency
- All blocks are locked at power-up or device reset.
- Block Erase, Full Chip Erase, (Page Buffer) Word Program Lockout during Power Transitions

■ Automated Erase/Program Algorithms
- 3.0V Low-Power 11µs/Word (Typ.) Programming
- 9.5V No Glue Logic 9µs/Word (Typ.) Production Programming and 0.8s Erase (Typ.)

■ Cross-Compatible Command Support
- Basic Command Set
- Common Flash Interface (CFI)

■ Extended Cycling Capability
- Minimum 100,000 Block Erase Cycles

■ 56-Lead TSOP (Normal Bend)

■ ETOX^{TM*} Flash Technology

■ Not designed or rated as radiation hardened

The product, which is 6-Plane Page Mode Dual Work (Simultaneous Read while Erase/Program) Flash memory, is a low power, high density, low cost, nonvolatile read/write storage solution for a wide range of applications. The product can operate at V_{CC}=2.7V-3.3V. Its low voltage operation capability greatly extends battery life for portable applications.

The product provides high performance asynchronous page mode. It allows code execution directly from Flash, thus eliminating time consuming wait states.

The memory array block architecture utilizes Enhanced Data Protection features, and provides separate Parameter and Main Blocks that provide maximum flexibility for safe nonvolatile code and data storage.

Fast program capability is provided through the use of high speed Page Buffer Program.

Special OTP (One Time Program) block provides an area to store permanent code such as an unique number.

* ETOX is a trademark of Intel Corporation.

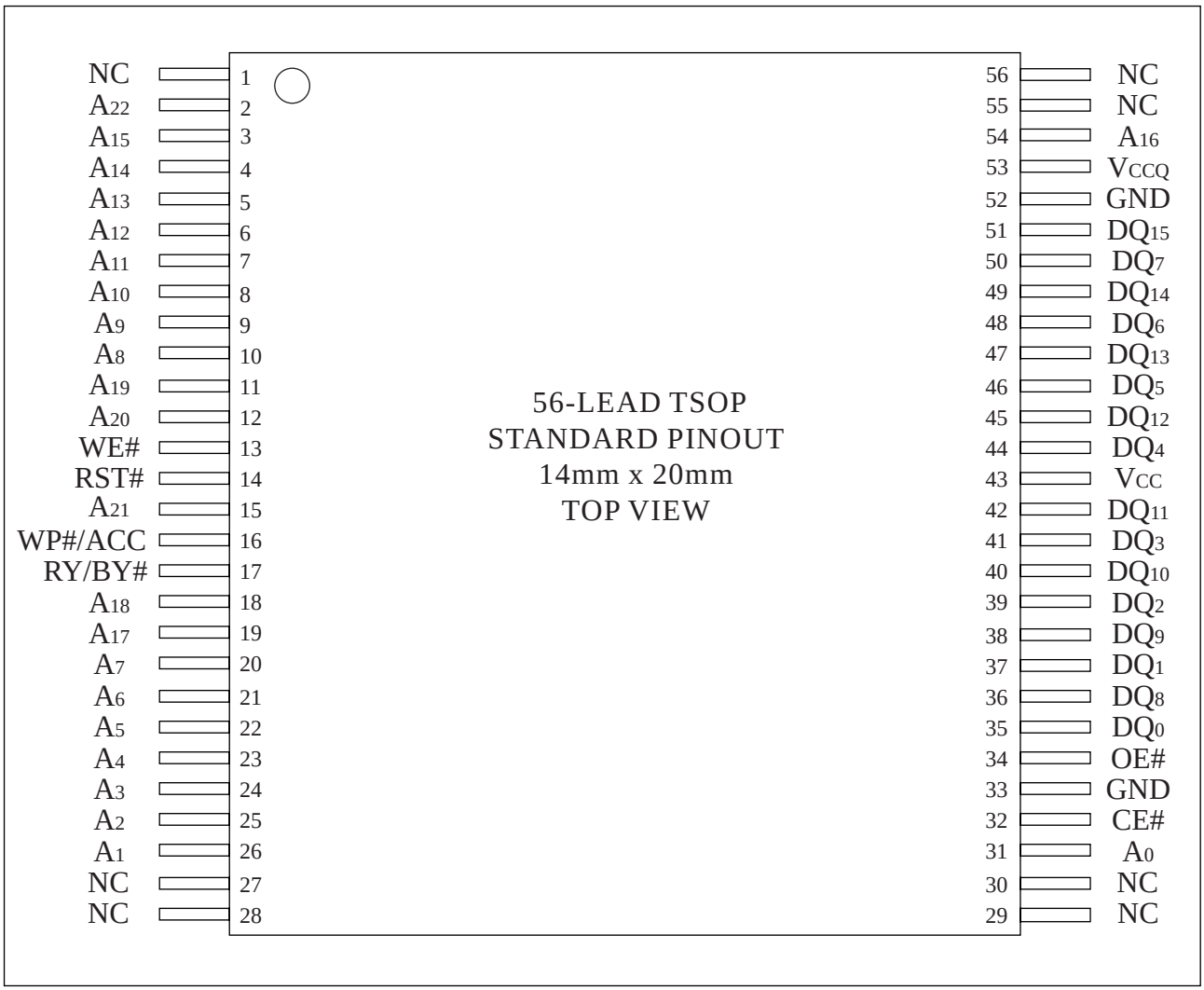


Figure 1. 56-Lead TSOP (Normal Bend) Pinout

Table 1. Pin Descriptions

Symbol	Type	Name and Function
A_{22}-A_0	INPUT	ADDRESS INPUTS: Inputs for addresses.
DQ_{15}-DQ_0	INPUT/ OUTPUT	DATA INPUTS/OUTPUTS: Inputs data and commands during CUI (Command User Interface) write cycles, outputs data during memory array, status register, query code and identifier code reads. Data pins float to high-impedance (High Z) when the chip or outputs are deselected. Data is internally latched during an erase or program cycle.
CE#	INPUT	CHIP ENABLE: Activates the device's control logic, input buffers, decoders and sense amplifiers. CE#-high (V_{IH}) deselects the device and reduces power consumption to standby levels.
RST#	INPUT	RESET: When low (V_{IL}), RST# resets internal automation and inhibits write operations which provides data protection. RST#-high (V_{IH}) enables normal operation. After power-up or reset mode, the device is automatically set to read array mode. RST# must be low during power-up/down.
OE#	INPUT	OUTPUT ENABLE: Gates the device's outputs during a read cycle.
WE#	INPUT	WRITE ENABLE: Controls writes to the CUI and array blocks. Addresses and data are latched on the rising edge of CE# or WE# (whichever goes high first).
WP#/ACC	INPUT/ SUPPLY	WRITE PROTECT: When WP#/ACC is V_{IL}, locked-down blocks cannot be unlocked. Erase or program operation can be executed to the blocks which are not locked and not locked-down. When WP#/ACC is V_{IH}, lock-down is disabled. Applying 9.5V±0.5V to WP#/ACC provides fast erasing or fast programming mode. In this mode, WP#/ACC is power supply pin. Applying 9.5V±0.5V to WP#/ACC during erase/program can only be done for a maximum of 1,000 cycles on each block. WP#/ ACC may be connected to 9.5V±0.5V for a total of 80 hours maximum. Use of this pin at 9.5V+0.5V beyond these limits may reduce block cycling capability or cause permanent damage.
RY/BY#	OPEN DRAIN OUTPUT	READY/BUSY#: Indicates the status of the internal WSM (Write State Machine). When low, WSM is performing an internal operation (block erase, full chip erase, (page buffer) program or OTP program). RY/BY#-High Z indicates that the WSM is ready for new commands, block erase is suspended and (page buffer) program is inactive, (page buffer) program is suspended, or the device is in reset mode.
V_{CC}	SUPPLY	DEVICE POWER SUPPLY (2.7V-3.3V): With $V_{CC} \leq V_{LKO}$, all write attempts to the flash memory are inhibited. Device operations at invalid V_{CC} voltage (see DC Characteristics) produce spurious results and should not be attempted.
V_{CCQ}	SUPPLY	INPUT/OUTPUT POWER SUPPLY (2.7V-3.3V): Power supply for all input/output pins.
GND	SUPPLY	GROUND: Do not float any ground pins.
NC		NO CONNECT: Lead is not internally connected; it may be driven or floated.

Table 2. Simultaneous Operation Modes Allowed with 6 Planes [1, 2]

IF ONE PLANE IS:	THEN THE MODES ALLOWED IN THE OTHER PLANE IS:										
	Read Array	Read ID/OTP	Read Status	Read Query	Word Program	Page Buffer Program	OTP Program	Block Erase	Full Chip Erase	Program Suspend	Block Erase Suspend
Read Array	X	X	X	X	X	X		X		X	X
Read ID/OTP	X	X	X	X	X	X		X		X	X
Read Status	X	X	X	X	X	X	X	X	X	X	X
Read Query	X	X	X	X	X	X		X		X	X
Word Program	X	X	X	X							X
Page Buffer Program	X	X	X	X							X
OTP Program			X								
Block Erase	X	X	X	X							
Full Chip Erase			X								
Program Suspend	X	X	X	X							X
Block Erase Suspend	X	X	X	X	X	X				X	

NOTES:
1. "X" denotes the operation available.
2. Dual Work Restrictions:
   Status register reflects WSM (Write State Machine) state.
   Only one plane can be erased or programmed at a time - no command queuing.
   Commands must be written to an address within the block targeted by that command.

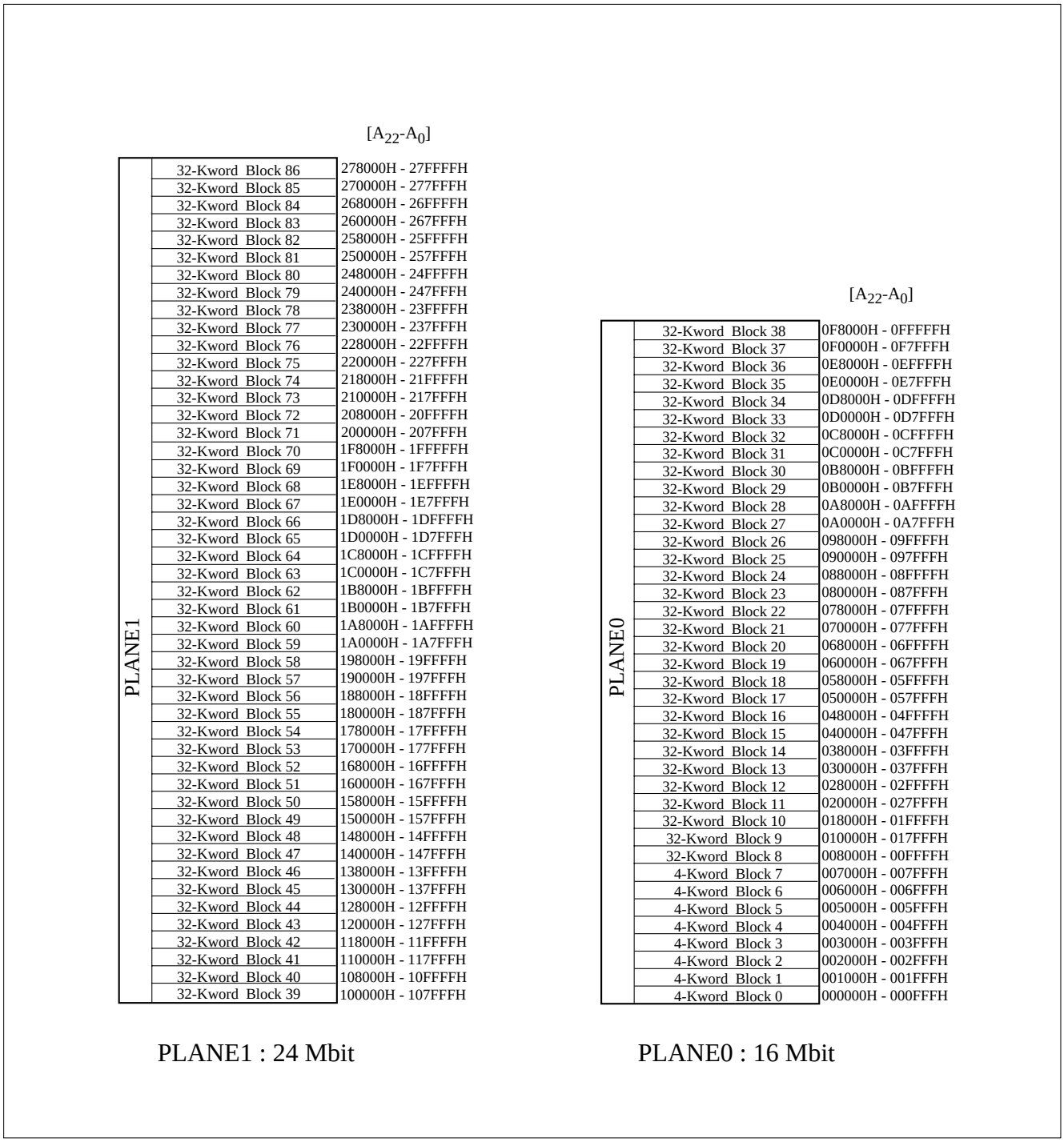


Figure 2.1. Memory Map (Bottom Parameter, Plane 0 and Plane 1)

		[A_{22}-A_0]
PLANE3	32-Kword Block 182	578000H - 57FFFFH
	32-Kword Block 181	570000H - 577FFFH
	32-Kword Block 180	568000H - 56FFFFH
	32-Kword Block 179	560000H - 567FFFH
	32-Kword Block 178	558000H - 55FFFFH
	32-Kword Block 177	550000H - 557FFFH
	32-Kword Block 176	548000H - 54FFFFH
	32-Kword Block 175	540000H - 547FFFH
	32-Kword Block 174	538000H - 53FFFFH
	32-Kword Block 173	530000H - 537FFFH
	32-Kword Block 172	528000H - 52FFFFH
	32-Kword Block 171	520000H - 527FFFH
	32-Kword Block 170	518000H - 51FFFFH
	32-Kword Block 169	510000H - 517FFFH
	32-Kword Block 168	508000H - 50FFFFH
	32-Kword Block 167	500000H - 507FFFH
	32-Kword Block 166	4F8000H - 4FFFFFH
	32-Kword Block 165	4F0000H - 4F7FFFH
	32-Kword Block 164	4E8000H - 4EFFFFH
	32-Kword Block 163	4E0000H - 4E7FFFH
	32-Kword Block 162	4D8000H - 4DFFFFH
	32-Kword Block 161	4D0000H - 4D7FFFH
	32-Kword Block 160	4C8000H - 4CFFFFH
	32-Kword Block 159	4C0000H - 4C7FFFH
	32-Kword Block 158	4B8000H - 4BFFFFH
	32-Kword Block 157	4B0000H - 4B7FFFH
	32-Kword Block 156	4A8000H - 4AFFFFH
	32-Kword Block 155	4A0000H - 4A7FFFH
	32-Kword Block 154	498000H - 49FFFFH
	32-Kword Block 153	490000H - 497FFFH
	32-Kword Block 152	488000H - 48FFFFH
	32-Kword Block 151	480000H - 487FFFH
	32-Kword Block 150	478000H - 47FFFFH
	32-Kword Block 149	470000H - 477FFFH
	32-Kword Block 148	468000H - 46FFFFH
	32-Kword Block 147	460000H - 467FFFH
	32-Kword Block 146	458000H - 45FFFFH
	32-Kword Block 145	450000H - 457FFFH
	32-Kword Block 144	448000H - 44FFFFH
	32-Kword Block 143	440000H - 447FFFH
	32-Kword Block 142	438000H - 43FFFFH
	32-Kword Block 141	430000H - 437FFFH
	32-Kword Block 140	428000H - 42FFFFH
	32-Kword Block 139	420000H - 427FFFH
	32-Kword Block 138	418000H - 41FFFFH
	32-Kword Block 137	410000H - 417FFFH
	32-Kword Block 136	408000H - 40FFFFH
	32-Kword Block 135	400000H - 407FFFH

PLANE3 : 24 Mbit

		[A_{22}-A_0]
PLANE2	32-Kword Block 134	3F8000H - 3FFFFFH
	32-Kword Block 133	3F0000H - 3F7FFFH
	32-Kword Block 132	3E8000H - 3EFFFFH
	32-Kword Block 131	3E0000H - 3E7FFFH
	32-Kword Block 130	3D8000H - 3DFFFFH
	32-Kword Block 129	3D0000H - 3D7FFFH
	32-Kword Block 128	3C8000H - 3CFFFFH
	32-Kword Block 127	3C0000H - 3C7FFFH
	32-Kword Block 126	3B8000H - 3BFFFFH
	32-Kword Block 125	3B0000H - 3B7FFFH
	32-Kword Block 124	3A8000H - 3AFFFFH
	32-Kword Block 123	3A0000H - 3A7FFFH
	32-Kword Block 122	398000H - 39FFFFH
	32-Kword Block 121	390000H - 397FFFH
	32-Kword Block 120	388000H - 38FFFFH
	32-Kword Block 119	380000H - 387FFFH
	32-Kword Block 118	378000H - 37FFFFH
	32-Kword Block 117	370000H - 377FFFH
	32-Kword Block 116	368000H - 36FFFFH
	32-Kword Block 115	360000H - 367FFFH
	32-Kword Block 114	358000H - 35FFFFH
	32-Kword Block 113	350000H - 357FFFH
	32-Kword Block 112	348000H - 34FFFFH
	32-Kword Block 111	340000H - 347FFFH
	32-Kword Block 110	338000H - 33FFFFH
	32-Kword Block 109	330000H - 337FFFH
	32-Kword Block 108	328000H - 32FFFFH
	32-Kword Block 107	320000H - 327FFFH
	32-Kword Block 106	318000H - 31FFFFH
	32-Kword Block 105	310000H - 317FFFH
	32-Kword Block 104	308000H - 30FFFFH
	32-Kword Block 103	300000H - 307FFFH
	32-Kword Block 102	2F8000H - 2FFFFFH
	32-Kword Block 101	2F0000H - 2F7FFFH
	32-Kword Block 100	2E8000H - 2EFFFFH
	32-Kword Block 99	2E0000H - 2E7FFFH
	32-Kword Block 98	2D8000H - 2DFFFFH
	32-Kword Block 97	2D0000H - 2D7FFFH
	32-Kword Block 96	2C8000H - 2CFFFFH
	32-Kword Block 95	2C0000H - 2C7FFFH
	32-Kword Block 94	2B8000H - 2BFFFFH
	32-Kword Block 93	2B0000H - 2B7FFFH
	32-Kword Block 92	2A8000H - 2AFFFFH
	32-Kword Block 91	2A0000H - 2A7FFFH
	32-Kword Block 90	298000H - 29FFFFH
	32-Kword Block 89	290000H - 297FFFH
	32-Kword Block 88	288000H - 28FFFFH
	32-Kword Block 87	280000H - 287FFFH

PLANE2 : 24 Mbit

Figure 2.2. Memory Map (Bottom Parameter, Plane 2 and Plane 3)

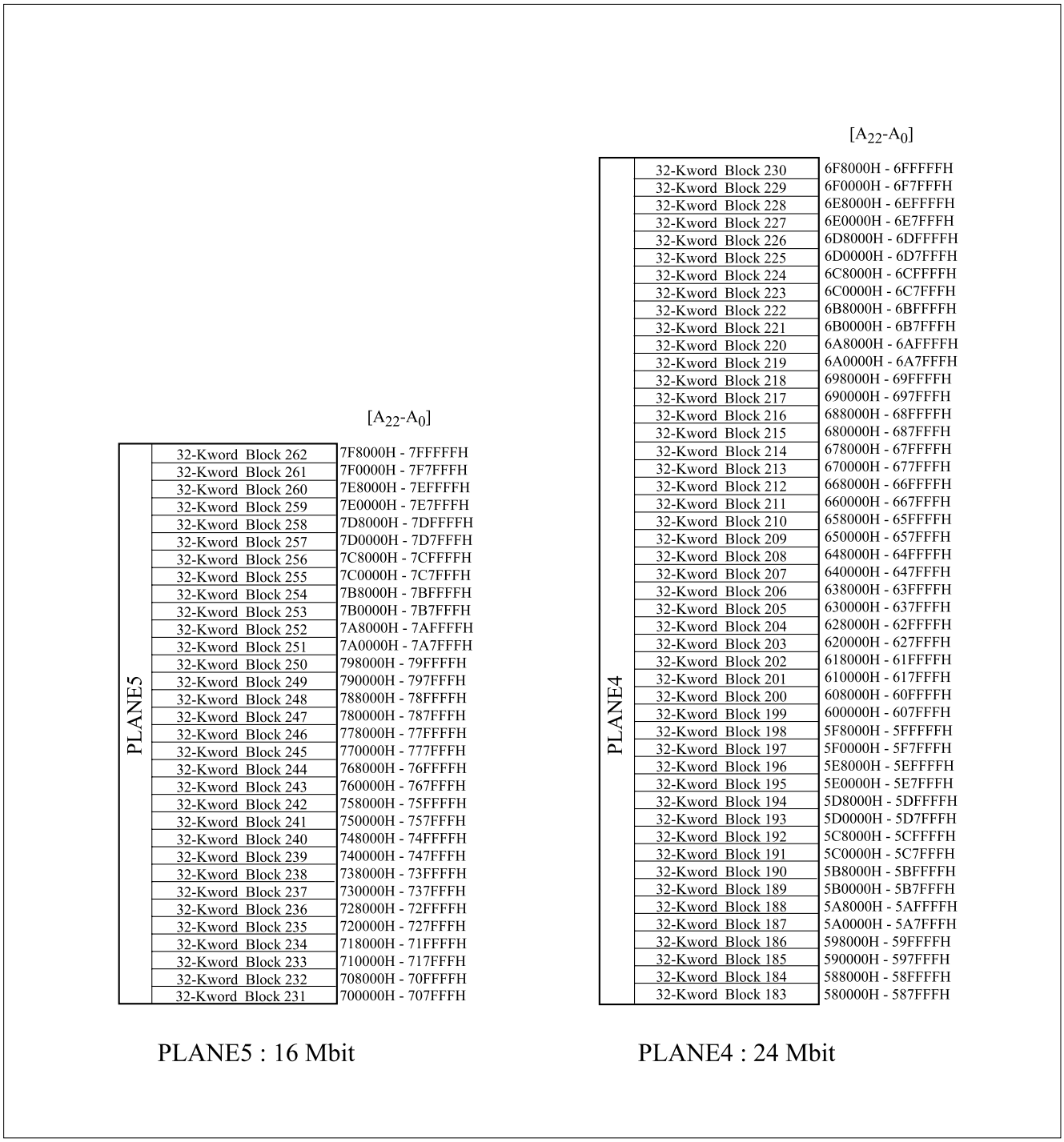


Figure 2.3. Memory Map (Bottom Parameter, Plane 4 and Plane 5)

Table 3. Identifier Codes and OTP Address for Read Operation

	Code	Address [A_{15}-A_0]	Data [DQ_{15}-DQ_0]	Notes
Manufacturer Code	Manufacturer Code	0000H	00B0H	1
Device Code	Device Code	0001H	0011H	1
Block Lock Configuration Code	Block is Unlocked	Block Address + 2	DQ_0 = 0	2, 3
	Block is Locked		DQ_0 = 1	2, 3
	Block is not Locked-Down		DQ_1 = 0	2, 3
	Block is Locked-Down		DQ_1 = 1	2, 3
OTP	OTP Lock	0080H	OTP-LK	1, 4
	OTP	0081-0088H	OTP	1, 5

NOTES:
1. A_{22}-A_{16} must be the address within the plane to which the Read Identifier Codes/OTP command (90H) has been written.
2. Block Address = The beginning location of a block address within the plane to which the Read Identifier Codes/OTP command (90H) has been written.
3. DQ_{15}-DQ_2 are reserved for future implementation.
4. OTP-LK=OTP Block Lock configuration.
5. OTP=OTP Block data.

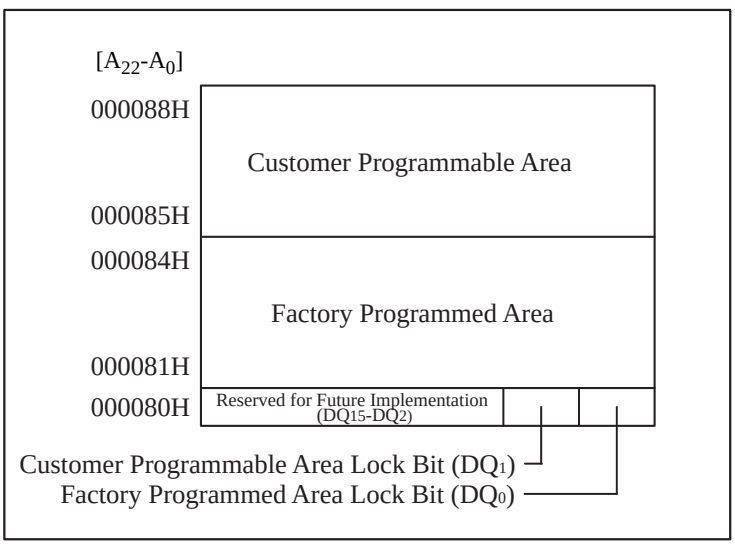


Figure 3. OTP Block Address Map for OTP Program
(The area outside 80H~88H cannot be used.)

Table 4. Bus Operation[1, 2]

Mode	Notes	RST#	CE#	OE#	WE#	Address	DQ_{15-0}	RY/BY# [8]
Read Array	6	V_{IH}	V_{IL}	V_{IL}	V_{IH}	X	D_{OUT}	High Z
Output Disable		V_{IH}	V_{IL}	V_{IH}	V_{IH}	X	High Z	X
Standby		V_{IH}	V_{IH}	X	X	X	High Z	X
Reset	3	V_{IL}	X	X	X	X	High Z	High Z
Read Identifier Codes/OTP	6	V_{IH}	V_{IL}	V_{IL}	V_{IH}	See Table 3	See Table 3	High Z
Read Query	6,7	V_{IH}	V_{IL}	V_{IL}	V_{IH}	X	D_{OUT}	High Z
Read Status Register	6	V_{IH}	V_{IL}	V_{IL}	V_{IH}	X	D_{OUT}	X
Write	4,5,6	V_{IH}	V_{IL}	V_{IH}	V_{IL}	X	D_{IN}	X

NOTES:
1. Refer to DC Characteristics for V_{IL} or V_{IH} voltages.
2. X can be V_{IL} or V_{IH} for control pins and addresses.
3. RST# at GND±0.2V ensures the lowest power consumption.
4. Command writes involving block erase, full chip erase, (page buffer) program or OTP program are reliably executed when V_{CC}=2.7V-3.3V.
5. Refer to Table 5 for valid D_{IN} during a write operation.
6. Never hold OE# low and WE# low at the same timing.
7. Query code = Common Flash Interface (CFI) code.
8. RY/BY# is V_{OL} when the WSM (Write State Machine) is executing internal block erase, full chip erase, (page buffer) program or OTP program algorithms. It is High Z during when the WSM is not busy, in block erase suspend mode (with program and page buffer program inactive), (page buffer) program suspend mode, or reset mode.

Table 5. Command Definitions(11)

Command	Bus Cycles Req'd	Notes	First Bus Cycle			Second Bus Cycle		
			Oper(1)	Addr(2)	Data	Oper(1)	Addr(2)	Data(3)
Read Array	1		Write	PA	FFH			
Read Identifier Codes/OTP	≥ 2	4	Write	PA	90H	Read	IA or OA	ID or OD
Read Query	≥ 2	4	Write	PA	98H	Read	QA	QD
Read Status Register	2		Write	PA	70H	Read	PA	SRD
Clear Status Register	1		Write	PA	50H			
Block Erase	2	5	Write	BA	20H	Write	BA	D0H
Full Chip Erase	2	5,9	Write	X	30H	Write	X	D0H
Program	2	5,6	Write	WA	40H or 10H	Write	WA	WD
Page Buffer Program	≥ 4	5,7	Write	WA	E8H	Write	WA	N-1
Block Erase and (Page Buffer) Program Suspend	1	8,9	Write	PA	B0H			
Block Erase and (Page Buffer) Program Resume	1	8,9	Write	PA	D0H			
Set Block Lock Bit	2		Write	BA	60H	Write	BA	01H
Clear Block Lock Bit	2	10	Write	BA	60H	Write	BA	D0H
Set Block Lock-down Bit	2		Write	BA	60H	Write	BA	2FH
OTP Program	2	9	Write	OA	C0H	Write	OA	OD

NOTES:
1. Bus operations are defined in Table 4.
2. All addresses which are written at the first bus cycle should be the same as the addresses which are written at the second bus cycle.
   X=Any valid address within the device.
   PA=Address within the selected plane.
   IA=Identifier codes address (See Table 3).
   QA=Query codes address.
   BA=Address within the block being erased, set/cleared block lock bit or set block lock-down bit.
   WA=Address of memory location for the Program command or the first address for the Page Buffer Program command.
   OA=Address of OTP block to be read or programmed (See Figure 3).
3. ID=Data read from identifier codes. (See Table 3).
   QD=Data read from query database.
   SRD=Data read from status register. See Table 9.1, Table 9.2 for a description of the status register bits.
   WD=Data to be programmed at location WA. Data is latched on the rising edge of WE# or CE# (whichever goes high first) during command write cycles.
   OD=Data within OTP block. Data is latched on the rising edge of WE# or CE# (whichever goes high first) during command write cycles.
   N-1=N is the number of the words to be loaded into a page buffer.
4. Following the Read Identifier Codes/OTP command, read operations access manufacturer code, device code, block lock configuration code and the data within OTP block (See Table 3).
   The Read Query command is available for reading CFI (Common Flash Interface) information.
5. Block erase, full chip erase or (page buffer) program cannot be executed when the selected block is locked. Unlocked block can be erased or programmed when RST# is V_{IH}.
6. Either 40H or 10H are recognized by the CUI (Command User Interface) as the program setup.

7. Following the third bus cycle, input the program sequential address and write data of "N" times. Finally, input the any valid address within the target block to be programmed and the confirm command (D0H).
8. If the program operation in one plane is suspended and the erase operation in other plane is also suspended, the suspended program operation will be resumed first.
9. Full chip erase and OTP program operations can not be suspended. The OTP Program command can not be accepted while the block erase operation is being suspended.
10. Following the Clear Block Lock Bit command, block which is not locked-down is unlocked when WP#/ACC is V_{IL}. When WP#/ACC is V_{IH}, lock-down bit is disabled and the selected block is unlocked regardless of lock-down configuration.
11. Commands other than those shown above are reserved by SHARP for future device implementations and should not be used.

Table 6. Functions of Block Lock[5] and Block Lock-Down

Current State					Erase/Program Allowed [2]
State	WP#/ACC	DQ_1[1]	DQ_0[1]	State Name	
[000]	0	0	0	Unlocked	Yes
[001][3]	0	0	1	Locked	No
[011]	0	1	1	Locked-down	No
[100]	1	0	0	Unlocked	Yes
[101][3]	1	0	1	Locked	No
[110][4]	1	1	0	Lock-down Disable	Yes
[111]	1	1	1	Lock-down Disable	No

NOTES:
1. DQ_0=1: a block is locked; DQ_0=0: a block is unlocked.
   DQ_1=1: a block is locked-down; DQ_1=0: a block is not locked-down.
2. Erase and program are general terms, respectively, to express: block erase, full chip erase and (page buffer) program operations.
3. At power-up or device reset, all blocks default to locked state and are not locked-down, that is, [001] (WP#/ACC=0) or [101] (WP#/ACC=1), regardless of the states before power-off or reset operation.
4. When WP#/ACC is driven to V_{IL} in [110] state, the state changes to [011] and the blocks are automatically locked.
5. OTP (One Time Program) block has the lock function which is different from those described above.

Table 7. Block Locking State Transitions upon Command Write[4]

Current State				Result after Lock Command Written (Next State)		
State	WP#/ACC	DQ_1	DQ_0	Set Lock[1]	Clear Lock[1]	Set Lock-down[1]
[000]	0	0	0	[001]	No Change	[011][2]
[001]	0	0	1	No Change[3]	[000]	[011]
[011]	0	1	1	No Change	No Change	No Change
[100]	1	0	0	[101]	No Change	[111][2]
[101]	1	0	1	No Change	[100]	[111]
[110]	1	1	0	[111]	No Change	[111][2]
[111]	1	1	1	No Change	[110]	No Change

NOTES:
1. "Set Lock" means Set Block Lock Bit command, "Clear Lock" means Clear Block Lock Bit command and "Set Lock-down" means Set Block Lock-Down Bit command.
2. When the Set Block Lock-Down Bit command is written to the unlocked block (DQ_0=0), the corresponding block is locked-down and automatically locked at the same time.
3. "No Change" means that the state remains unchanged after the command written.
4. In this state transitions table, assumes that WP#/ACC is not changed and fixed V_{IL} or V_{IH}.

Table 8. Block Locking State Transitions upon WP#/ACC Transition[4]

Previous State	Current State				Result after WP#/ACC Transition (Next State)	
	State	WP#/ACC	DQ_1	DQ_0	WP#/ACC=0→1[1]	WP#/ACC=1→0[1]
-	[000]	0	0	0	[100]	-
-	[001]	0	0	1	[101]	-
[110][2]	[011]	0	1	1	[110]	-
Other than [110][2]					[111]	-
-	[100]	1	0	0	-	[000]
-	[101]	1	0	1	-	[001]
-	[110]	1	1	0	-	[011][3]
-	[111]	1	1	1	-	[011]

NOTES:
1. "WP#/ACC=0→1" means that WP#/ACC is driven to V_{IH} and "WP#/ACC=1→0" means that WP#/ACC is driven to V_{IL}.
2. State transition from the current state [011] to the next state depends on the previous state.
3. When WP#/ACC is driven to V_{IL} in [110] state, the state changes to [011] and the blocks are automatically locked.
4. In this state transitions table, assumes that lock configuration commands are not written in previous, current and next state.

Table 9.1. Status Register Definition

GWSMS	GBESS	GBEFCES	GPBPOPS	GWPACCS	GPBPSS	GDPS	R
15	14	13	12	11	10	9	8
PWSMS	GBESS	GBEFCES	GPBPOPS	GWPACCS	GPBPSS	GDPS	R
7	6	5	4	3	2	1	0

	NOTES:
SR.7 = PLANE WRITE STATE MACHINE STATUS (PWSMS) 1 = Ready 0 = Busy	Status Register indicates the status of the WSM (Write State Machine). However, SR.7 indicates the status of WSM in each plane. Even if the SR.7 is "1", the WSM may be occupied by the other plane.
SR.6 = GLOBAL BLOCK ERASE SUSPEND STATUS (GBESS) 1 = Block Erase Suspended 0 = Block Erase in Progress/Completed	In the plane to which the command is issued, Check SR.7 or RY/BY# to determine block erase, full chip erase, (page buffer) program or OTP program completion. SR.6 - SR.1 are invalid while SR.7="0".
SR.5 = GLOBAL BLOCK ERASE AND FULL CHIP ERASE STATUS (GBEFCES) 1 = Error in Block Erase or Full Chip Erase 0 = Successful Block Erase or Full Chip Erase	If both SR.5 and SR.4 are "1"s after a block erase, full chip erase, (page buffer) program, set/clear block lock bit, set block lock-down bit attempt, an improper command sequence was entered.
SR.4 = GLOBAL (PAGE BUFFER) PROGRAM AND OTP PROGRAM STATUS (GPBPOPS) 1 = Error in (Page Buffer) Program or OTP Program 0 = Successful (Page Buffer) Program or OTP Program	
SR.3 = GLOBAL WP#/ACC STATUS (GWPACCS) 1 = V_{CCQ}+0.4V < WP#/ACC < 9.0V Detect, Operation Abort 0 = WP#/ACC OK	SR.3 does not provide a continuous indication of WP#/ACC level. The WSM interrogates and indicates the WP#/ACC level only after Block Erase, Full Chip Erase, (Page Buffer) Program or OTP Program command sequences. SR.3 is not guaranteed to report accurate feedback when WP#/ACC≠V_{ACCH}.
SR.2 = GLOBAL (PAGE BUFFER) PROGRAM SUSPEND STATUS (GPBPSS) 1 = (Page Buffer) Program Suspended 0 = (Page Buffer) Program in Progress/Completed	SR.1 does not provide a continuous indication of block lock bit. The WSM interrogates the block lock bit only after Block Erase, Full Chip Erase, (Page Buffer) Program or OTP Program command sequences. It informs the system, depending on the attempted operation, if the block lock bit is set. Reading the block lock configuration codes after writing the Read Identifier Codes/OTP command indicates block lock bit status.
SR.1 = GLOBAL DEVICE PROTECT STATUS (GDPS) 1 = Erase or Program Attempted on a Locked Block, Operation Abort 0 = Unlocked	
SR.0 = RESERVED FOR FUTURE ENHANCEMENTS (R)	SR.0 is reserved for future use and should be masked out when polling the status register.

Table 9.2. Status Register Definition (Continued)

	NOTES:
SR.15 = GLOBAL WRITE STATE MACHINE STATUS (GWSMS) 1 = Ready 0 = Busy	Status Register SR.15-SR.9 indicates the status of the WSM. Check SR.15 or RY/BY# to determine block erase, full chip erase, (page buffer) program or OTP program completion. SR.14 - SR.9 are invalid while SR.15="0".
SR.14 = GLOBAL BLOCK ERASE SUSPEND STATUS (GBESS) 1 = Block Erase Suspended 0 = Block Erase in Progress/Completed	
SR.13 = GLOBAL BLOCK ERASE AND FULL CHIP ERASE STATUS (GBEFCES) 1 = Error in Block Erase or Full Chip Erase 0 = Successful Block Erase or Full Chip Erase	If both SR.13 and SR.12 are "1"s after a block erase, full chip erase, (page buffer) program, set/clear block lock bit, set block lock-down bit attempt, an improper command sequence was entered.
SR.12 = GLOBAL (PAGE BUFFER) PROGRAM AND OTP PROGRAM STATUS (GPBPOPS) 1 = Error in (Page Buffer) Program or OTP Program 0 = Successful (Page Buffer) Program or OTP Program	
SR.11 = GLOBAL WP#/ACC STATUS (GWPACCS) 1 = V_{CCQ}+0.4V < WPP#/ACC < 9.0V Detect, Operation Abort 0 = WP#/ACC OK	SR.11 does not provide a continuous indication of WP#/ACC level. The WSM interrogates and indicates the WP#/ACC level only after Block Erase, Full Chip Erase, (Page Buffer) Program or OTP Program command sequences. SR.11 is not guaranteed to report accurate feedback when WP#/ACC≠V_{ACCH}.
SR.10 = GLOBAL (PAGE BUFFER) PROGRAM SUSPEND STATUS (GPBPSS) 1 = (Page Buffer) Program Suspended 0 = (Page Buffer) Program in Progress/Completed	
SR.9 = GLOBAL DEVICE PROTECT STATUS (GDPS) 1 = Erase or Program Attempted on a Locked Block, Operation Abort 0 = Unlocked	SR.9 does not provide a continuous indication of block lock bit. The WSM interrogates the block lock bit only after Block Erase, Full Chip Erase, (Page Buffer) Program or OTP Program command sequences. It informs the system, depending on the attempted operation, if the block lock bit is set. Reading the block lock configuration codes after writing the Read Identifier Codes/OTP command indicates block lock bit status.
SR.8 = RESERVED FOR FUTURE ENHANCEMENTS (R)	SR.8 is reserved for future use and should be masked out when polling the status register.

Table 10. Extended Status Register Definition

R	R	R	R	R	R	R	R
15	14	13	12	11	10	9	8
SMS	R	R	R	R	R	R	R
7	6	5	4	3	2	1	0

XSR.15-8 = RESERVED FOR FUTURE ENHANCEMENTS (R)

XSR.7 = STATE MACHINE STATUS (SMS)
1 = Page Buffer Program available
0 = Page Buffer Program not available

XSR.6-0 = RESERVED FOR FUTURE ENHANCEMENTS (R)

NOTES:

After issue a Page Buffer Program command (E8H), XSR.7="1" indicates that the entered command is accepted. If XSR.7 is "0", the command is not accepted and a next Page Buffer Program command (E8H) should be issued again to check if page buffer is available or not.

XSR.15-8 and XSR.6-0 are reserved for future use and should be masked out when polling the extended status register.

1 Electrical Specifications

1.1 Absolute Maximum Ratings*

Operating Temperature

During Read, Erase and Program ...-40°C to +85°C (1)

Storage Temperature

During under Bias..... -40°C to +85°C

During non Bias..... -65°C to +125°C

Voltage On Any Pin (except V_{CC}, V_{CCQ} and WP#/ACC)

.....-0.5V to V_{CCQ}+0.5V (2)

V_{CC} and V_{CCQ} Supply Voltage ..... -0.2V to +3.7V (2)

WP#/ACC Supply Voltage ..... -0.2V to +10.3V (2, 3, 4)

Output Short Circuit Current.....100mA (5)

**WARNING:* Stressing the device beyond the "Absolute Maximum Ratings" may cause permanent damage. These are stress ratings only. Operation beyond the "Operating Conditions" is not recommended and extended exposure beyond the "Operating Conditions" may affect device reliability.

NOTES:

1. Operating temperature is for extended temperature product defined by this specification.
2. All specified voltages are with respect to GND. Minimum DC voltage is -0.5V on input/output pins and -0.2V on V_{CC}, V_{CCQ} and WP#/ACC pins. During transitions, this level may undershoot to -2.0V for periods <20ns. Maximum DC voltage on input/output pins is V_{CC}+0.5V which, during transitions, may overshoot to V_{CC}+2.0V for periods <20ns.
3. Maximum DC voltage on WP#/ACC may overshoot to +11.0V for periods <20ns.
4. WP#/ACC erase/program voltage is normally 2.7V-3.3V. Applying 9.0V-10.0V to WP#/ACC during erase/program can be done for a maximum of 1,000 cycles on the main blocks and 1,000 cycles on the parameter blocks. WP#/ACC may be connected to 9.0V-10.0V for a total of 80 hours maximum.
5. Output shorted for no more than one second. No more than one output shorted at a time.

1.2 Operating Conditions

Parameter	Symbol	Min.	Typ.	Max.	Unit	Notes
Operating Temperature	T_A	-40	+25	+85	°C	
V_{CC} Supply Voltage	V_{CC}	2.7	3.0	3.3	V	1
I/O Supply Voltage	V_{CCQ}	2.7	3.0	3.3	V	1
WP#/ACC Voltage when Used as a Logic Control	V_{IL}	-0.2		0.4	V	1
	V_{IH}	2.4		V_{CCQ} + 0.4	V	
WP#/ACC Supply Voltage	V_{ACCH}	9.0	9.5	10.0	V	1, 2
Main Block Erase Cycling: WP#/ACC=V_{IL} or V_{IH}		100,000			Cycles	
Parameter Block Erase Cycling: WP#/ACC=V_{IL} or V_{IH}		100,000			Cycles	
Main Block Erase Cycling: WP#/ACC=V_{ACCH}, 80 hrs.				1,000	Cycles	
Parameter Block Erase Cycling: WP#/ACC=V_{ACCH}, 80 hrs.				1,000	Cycles	
Maximum WP#/ACC hours at V_{ACCH}				80	Hours	

NOTES:

1. See DC Characteristics tables for voltage range-specific specification.
2. Applying WP#/ACC=9.0V-10.0V during a erase or program can be done for a maximum of 1,000 cycles on the main blocks and 1,000 cycles on the parameter blocks. A permanent connection to WP#/ACC=9.0V-10.0V is not allowed and can cause damage to the device.

1.2.1 Capacitance (1) (T_A=+25°C, f=1MHz)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input Capacitance	C_{IN}	V_{IN}=0.0V		4	7	pF
WP#/ACC Input Capacitance	C_{IN}	V_{IN}=0.0V		18	22	pF
Output Capacitance	C_{OUT}	V_{OUT}=0.0V		6	10	pF

NOTE:
1. Sampled, not 100% tested.

1.2.2 AC Input/Output Test Conditions

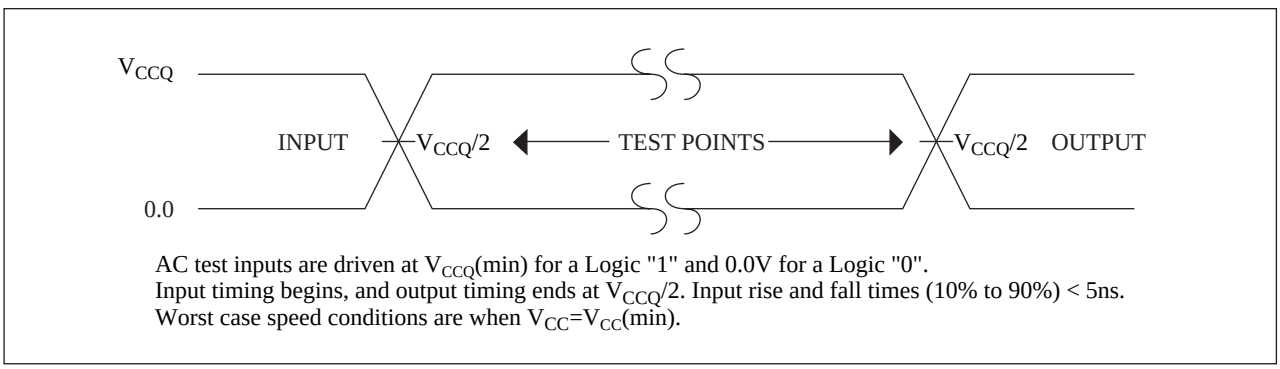


Figure 4. Transient Input/Output Reference Waveform for V_{CC}=2.7V-3.3V

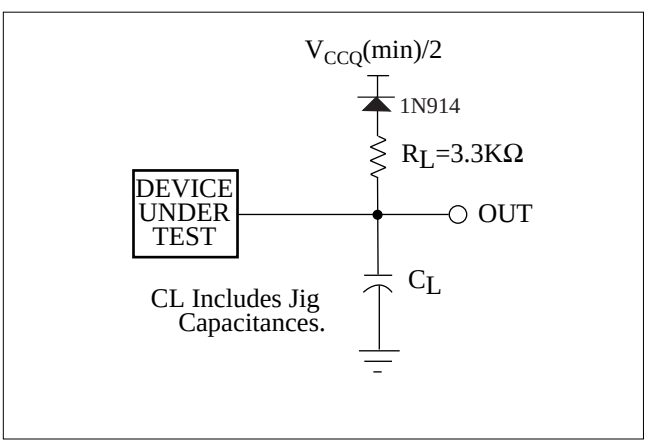


Figure 5. Transient Equivalent Testing Load Circuit

Table 11. Test Configuration Capacitance Loading Value

Test Configuration	C_L (pF)
V_{CC}=2.7V-3.3V	50

1.2.3 DC Characteristics

V_{CC}=2.7V-3.3V

Symbol	Parameter	Notes	Min.	Typ.	Max.	Unit	Test Conditions
I_{LI}	Input Load Current	1	-1.0		+1.0	µA	V_{CC}=V_{CC}Max., V_{CCQ}=V_{CCQ}Max., V_{IN}/V_{OUT}=V_{CCQ} or GND
I_{LO}	Output Leakage Current	1	-1.0		+1.0	µA	
I_{CCS}	V_{CC} Standby Current	1,7,8		9	40	µA	V_{CC}=V_{CC}Max., CE#=RST#= V_{CCQ}±0.2V, WP#/ACC=V_{CCQ} or GND
I_{CCAS}	V_{CC} Automatic Power Savings Current	1,3,7		9	40	µA	V_{CC}=V_{CC}Max., CE#=GND±0.2V, WP#/ACC=V_{CCQ} or GND
I_{CCD}	V_{CC} Reset Current	1,7		9	40	µA	RST#=GND±0.2V
I_{CCR}	Average V_{CC} Read Current Normal Mode	1,6,7		20	30	mA	V_{CC}=V_{CC}Max., CE#=V_{IL}, OE#=V_{IH}, f=5MHz
	Average V_{CC} Read Current Page Mode (8 Word Read)	1,6,7		5	10	mA	
I_{CCW}	V_{CC} (Page Buffer) Program Current	1,4,6,7		20	60	mA	WP#/ACC=V_{IL} or V_{IH}
		1,4,6,7		10	20	mA	WP#/ACC=V_{ACCH}
I_{CCE}	V_{CC} Block Erase, Full Chip Erase Current	1,4,6,7		10	30	mA	WP#/ACC=V_{IL} or V_{IH}
		1,4,6,7		4	10	mA	WP#/ACC=V_{ACCH}
I_{CCWS} I_{CCES}	V_{CC} (Page Buffer) Program or Block Erase Suspend Current	1,2,6,7		10	200	µA	CE#=V_{IH}
I_{ACCS} I_{ACCR}	WP#/ACC Standby or Read Current	1,5,6,7		2	5	µA	WP#/ACC≤V_{CC}
I_{ACCW}	WP#/ACC (Page Buffer) Program Current	1,4,5,6,7		2	5	µA	WP#/ACC=V_{IL} or V_{IH}
		1,4,5,6,7		10	30	mA	WP#/ACC=V_{ACCH}
I_{ACCE}	WP#/ACC Block Erase, Full Chip Erase Current	1,4,5,6,7		2	5	µA	WP#/ACC=V_{IL} or V_{IH}
		1,4,5,6,7		5	15	mA	WP#/ACC=V_{ACCH}
I_{ACCWS}	WP#/ACC (Page Buffer) Program Suspend Current	1,5,6,7		2	5	µA	WP#/ACC=V_{IL} or V_{IH}
		1,5,6,7		10	200	µA	WP#/ACC=V_{ACCH}
I_{ACCES}	WP#/ACC Block Erase Suspend Current	1,5,6,7		2	5	µA	WP#/ACC=V_{IL} or V_{IH}
		1,5,6,7		10	200	µA	WP#/ACC=V_{ACCH}

DC Characteristics (Continued)

V_{CC}=2.7V-3.3V

Symbol	Parameter	Notes	Min.	Typ.	Max.	Unit	Test Conditions
V_{IL}	Input Low Voltage	5	-0.4		0.4	V	
V_{IH}	Input High Voltage	4	2.4		V_{CCQ} + 0.4	V	
V_{OL}	Output Low Voltage	4,8			0.2	V	V_{CC}=V_{CC}Min., V_{CCQ}=V_{CCQ}Min., I_{OL}=100µA
V_{OH}	Output High Voltage	4	V_{CCQ} -0.2			V	V_{CC}=V_{CC}Min., V_{CCQ}=V_{CCQ}Min., I_{OH}=-100µA
V_{ACCH}	WP#/ACC during Block Erase, Full Chip Erase, (Page Buffer) Program or OTP Program Operations	5	9.0	9.5	10.0	V	
V_{LKO}	V_{CC} Lockout Voltage		1.5			V	

NOTES:
1. All currents are in RMS unless otherwise noted. Typical values are the reference values at V_{CC}=3.0V, V_{CCQ}=3.0V and T_A=+25°C unless V_{CC} is specified.
2. I_{CCWS} and I_{CCES} are specified with the device de-selected. If read or (page buffer) program is executed while in block erase suspend mode, the device's current draw is the sum of I_{CCES} and I_{CCR} or I_{CCW}. If read is executed while in (page buffer) program suspend mode, the device's current draw is the sum of I_{CCWS} and I_{CCR}.
3. The Automatic Power Savings (APS) feature automatically places the device in power save mode after read cycle completion. Standard address access timings (t_{AVQV}) provide new data when addresses are changed.
4. Sampled, not 100% tested.
5. Applying 9.5V±0.5V to WP#/ACC provides fast erasing or fast programming mode. In this mode, WP#/ACC is power supply pin and supplies the memory cell current for block erasing and (page buffer) programming. Use similar power supply trace widths and layout considerations given to the V_{CC} power bus.
   Applying 9.5V±0.5V to WP#/ACC during erase/program can only be done for a maximum of 1,000 cycles on each block. WP#/ACC may be connected to 9.5V±0.5V for a total of 80 hours maximum.
6. The operating current in dual work is the sum of the operating current (read, erase, program) in each plane.
7. For all pins other than those shown in test conditions, input level is V_{CCQ} or GND.
8. Includes RY/BY#.

1.2.4 AC Characteristics - Read-Only Operations(1)

V_{CC}=2.7V-3.3V, T_A=-40°C to +85°C

Symbol	Parameter	Notes	Min.	Max.	Unit
t_{AVAV}	Read Cycle Time		75		ns
t_{AVQV}	Address to Output Delay			75	ns
t_{ELQV}	CE# to Output Delay	3		75	ns
t_{APA}	Page Address Access Time			25	ns
t_{GLQV}	OE# to Output Delay	3		20	ns
t_{PHQV}	RST# High to Output Delay			150	ns
t_{EHQZ}, t_{GHQZ}	CE# or OE# to Output in High Z, Whichever Occurs First	2		20	ns
t_{ELQX}	CE# to Output in Low Z	2	0		ns
t_{GLQX}	OE# to Output in Low Z	2	0		ns
t_{OH}	Output Hold from First Occurring Address, CE# or OE# change	2	0		ns
t_{AVEL}, t_{AVGL}	Address Setup to CE#, OE# Going Low for Reading Status Register	4, 6	10		ns
t_{ELAX}, t_{GLAX}	Address Hold from CE#, OE# Going Low for Reading Status Register	5, 6	10		ns
t_{EHEL}, t_{GHGL}	CE#, OE# Pulse Width High for Reading Status Register	6	20		ns

NOTES:
1. See AC input/output reference waveform for timing measurements and maximum allowable input slew rate.
2. Sampled, not 100% tested.
3. OE# may be delayed up to $t_{ELQV} - t_{GLQV}$ after the falling edge of CE# without impact to t_{ELQV}.
4. Address setup time (t_{AVEL}, t_{AVGL}) is defined from the falling edge of CE# or OE# (whichever goes low last).
5. Address hold time (t_{ELAX}, t_{GLAX}) is defined from the falling edge of CE# or OE# (whichever goes low last).
6. Specifications t_{AVEL}, t_{AVGL}, t_{ELAX}, t_{GLAX} and t_{EHEL}, t_{GHGL} for read operations apply to only status register read operations.

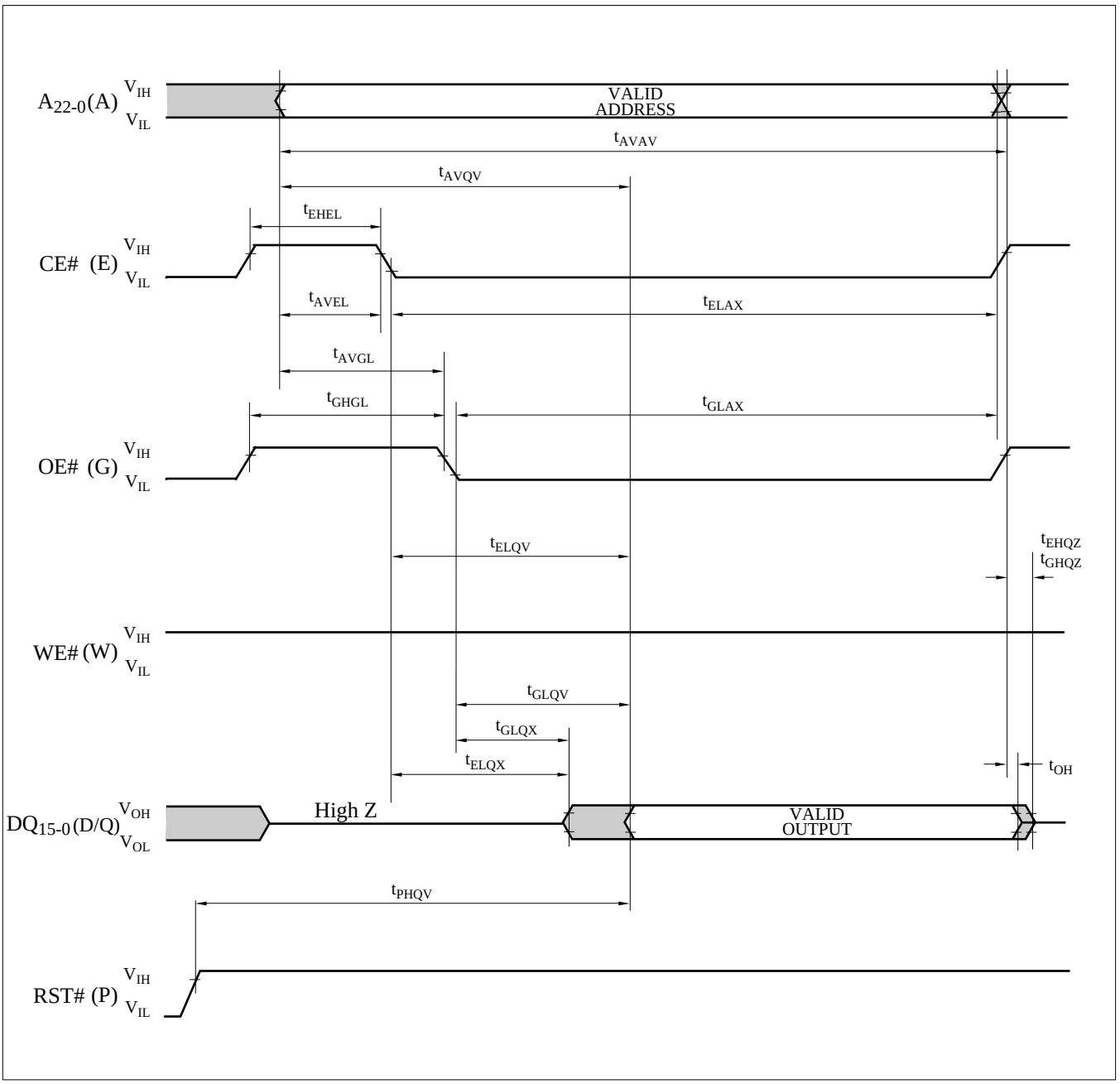


Figure 6. AC Waveform for Single Asynchronous Read Operations
from Status Register, Identifier Codes, OTP Block or Query Code

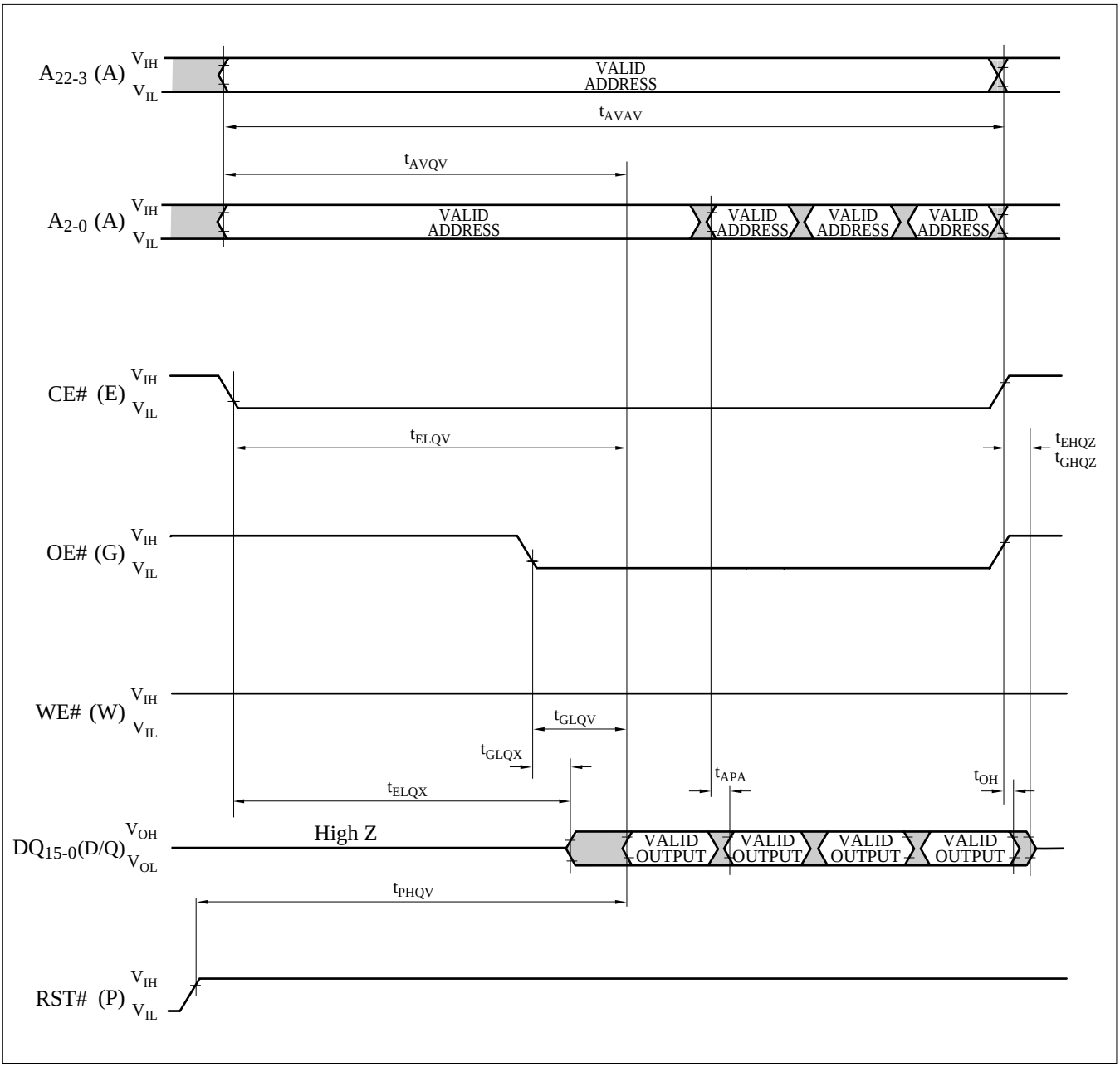


Figure 7. AC Waveform for Asynchronous 4-Word Page Mode
Read Operations from Main Blocks or Parameter Blocks

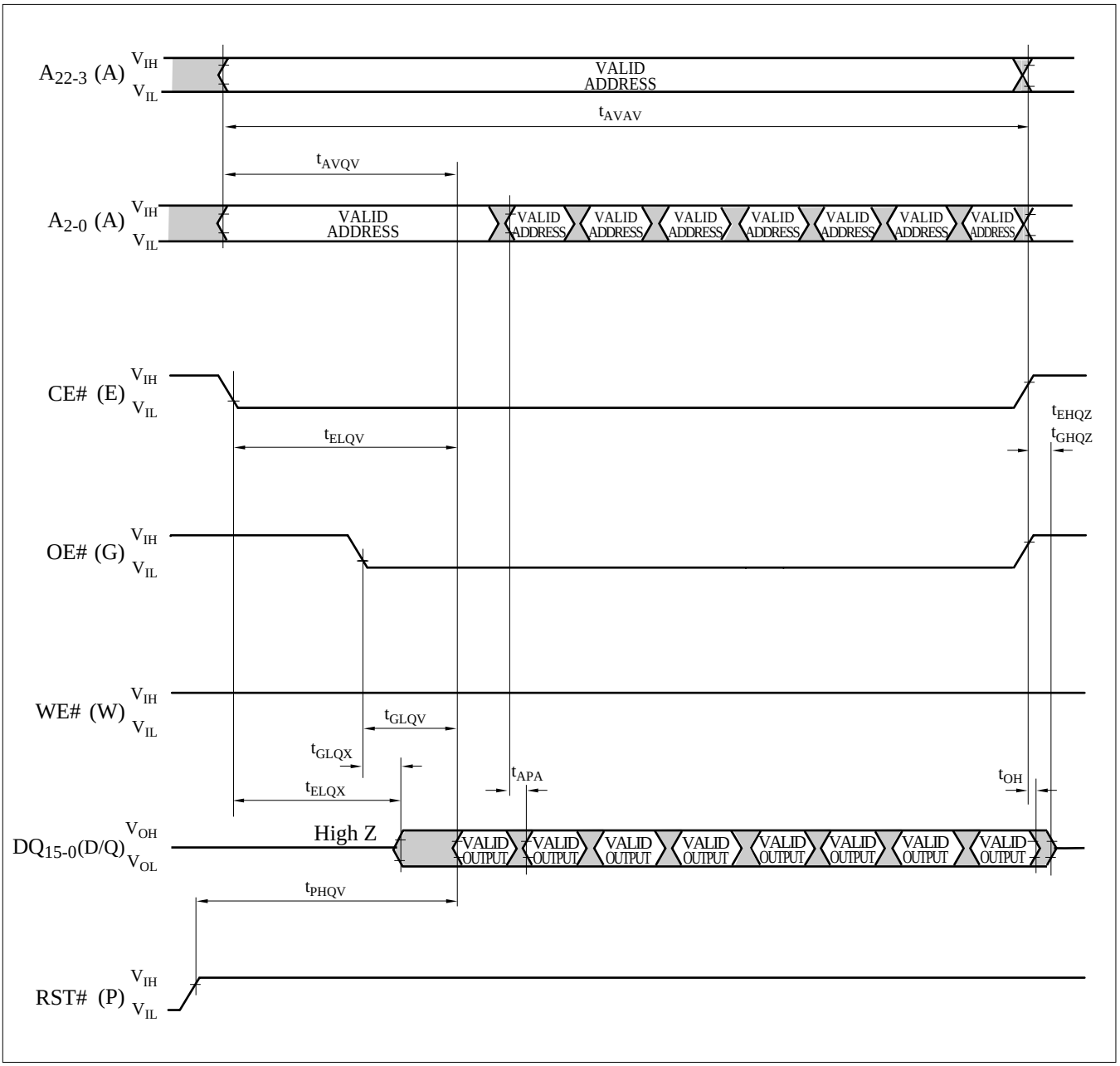


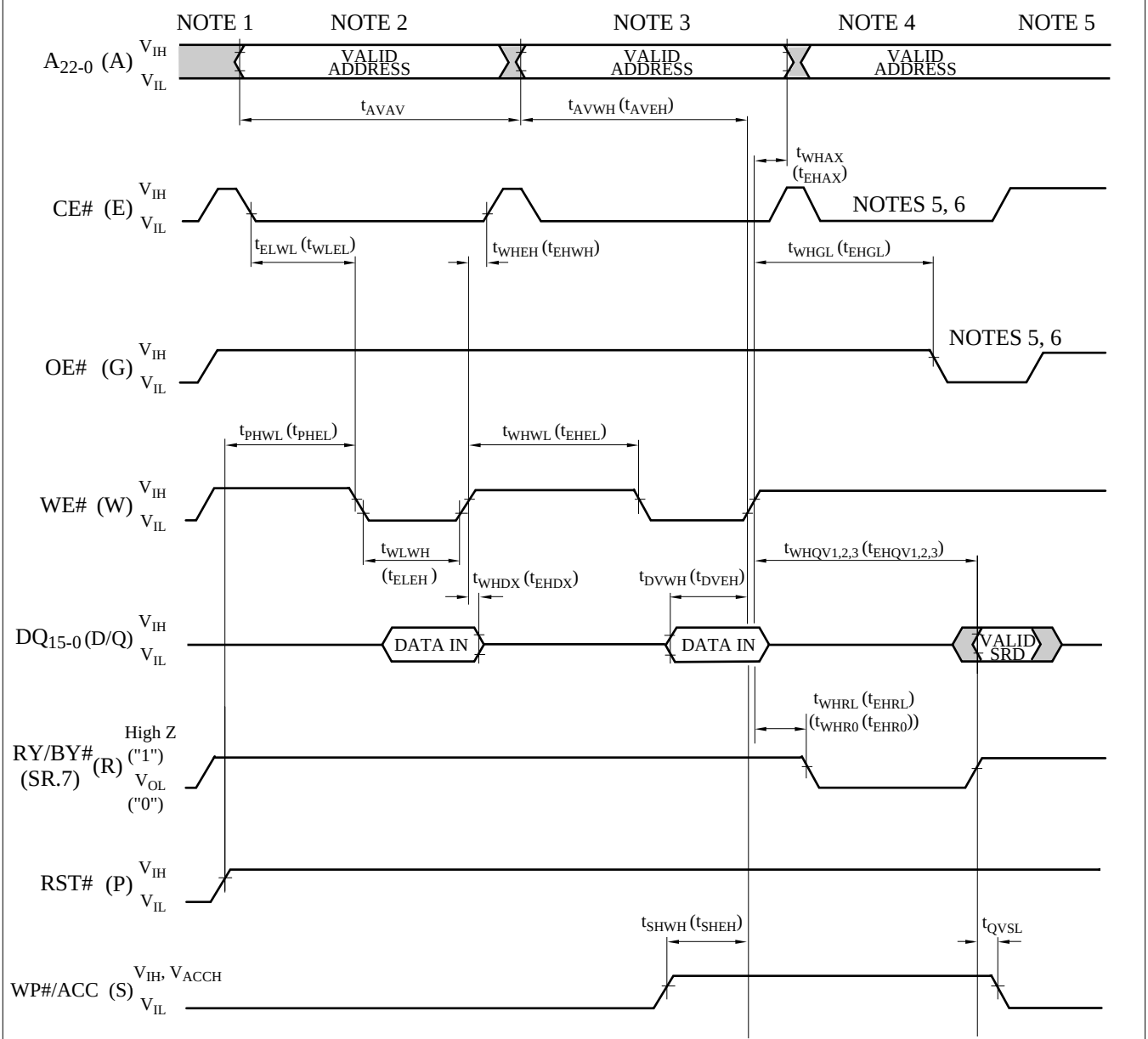
Figure 8. AC Waveform for Asynchronous 8-Word Page Mode
Read Operations from Main Blocks or Parameter Blocks

1.2.5 AC Characteristics - Write Operations[1, 2]

V_{CC}=2.7V-3.3V, T_A=-40°C to +85°C

Symbol	Parameter		Notes	Min.	Max.	Unit
t_{AVAV}	Write Cycle Time			75		ns
t_{PHWL} (t_{PHEL})	RST# High Recovery to WE# (CE#) Going Low		3	150		ns
t_{ELWL} (t_{WLEL})	CE# (WE#) Setup to WE# (CE#) Going Low			0		ns
t_{WLWH} (t_{ELEH})	WE# (CE#) Pulse Width		4	50		ns
t_{DVWH} (t_{DVEH})	Data Setup to WE# (CE#) Going High		7	40		ns
t_{AVWH} (t_{AVEH})	Address Setup to WE# (CE#) Going High		7	40		ns
t_{WHEH} (t_{EHWH})	CE# (WE#) Hold from WE# (CE#) High			0		ns
t_{WHDX} (t_{EHDX})	Data Hold from WE# (CE#) High			0		ns
t_{WHAX} (t_{EHAX})	Address Hold from WE# (CE#) High			0		ns
t_{WHWL} (t_{EHEL})	WE# (CE#) Pulse Width High		5	25		ns
t_{SHWH} (t_{SHEH})	WP#/ACC High Setup to WE# (CE#) Going High	WP#/ACC=V_{IH}	3	0		ns
		WP#/ACC=V_{ACCH}		200		
t_{WHGL} (t_{EHGL})	Write Recovery before Read			30		ns
t_{QVSL}	WP#/ACC High Hold from Valid SRD, RY/BY# High Z		3	0		ns
t_{WHR0} (t_{EHR0})	WE# (CE#) High to SR.7 Going "0"		3, 6		t_{AVQV} +50	ns
t_{WHRL} (t_{EHRL})	WE# (CE#) High to RY/BY# Going Low		3		100	ns

NOTES:
1. The timing characteristics for reading the status register during block erase, full chip erase, (page buffer) program and OTP program operations are the same as during read-only operations. Refer to AC Characteristics for read-only operations.
2. A write operation can be initiated and terminated with either CE# or WE#.
3. Sampled, not 100% tested.
4. Write pulse width (t_{WP}) is defined from the falling edge of CE# or WE# (whichever goes low last) to the rising edge of CE# or WE# (whichever goes high first). Hence, $t_{WP}=t_{WLWH}=t_{ELEH}=t_{WLEH}=t_{ELWH}$.
5. Write pulse width high (t_{WPH}) is defined from the rising edge of CE# or WE# (whichever goes high first) to the falling edge of CE# or WE# (whichever goes low last). Hence, $t_{WPH}=t_{WHWL}=t_{EHEL}=t_{WHEL}=t_{EHWL}$.
6. t_{WHR0} (t_{EHR0}) after the Read Query or Read Identifier Codes/OTP command=t_{AVQV}+100ns.
7. Refer to Table 5 for valid address and data for block erase, full chip erase, (page buffer) program, OTP program or lock bit configuration.



NOTES:
1. V_{CC} power-up and standby.
2. Write each first cycle command.
3. Write each second cycle command or valid address and data.
4. Automated erase or program delay.
5. Read status register data.
6. For read operation, OE# and CE# must be driven active, and WE# de-asserted.

Figure 9. AC Waveform for Write Operations

1.2.6 Reset Operations

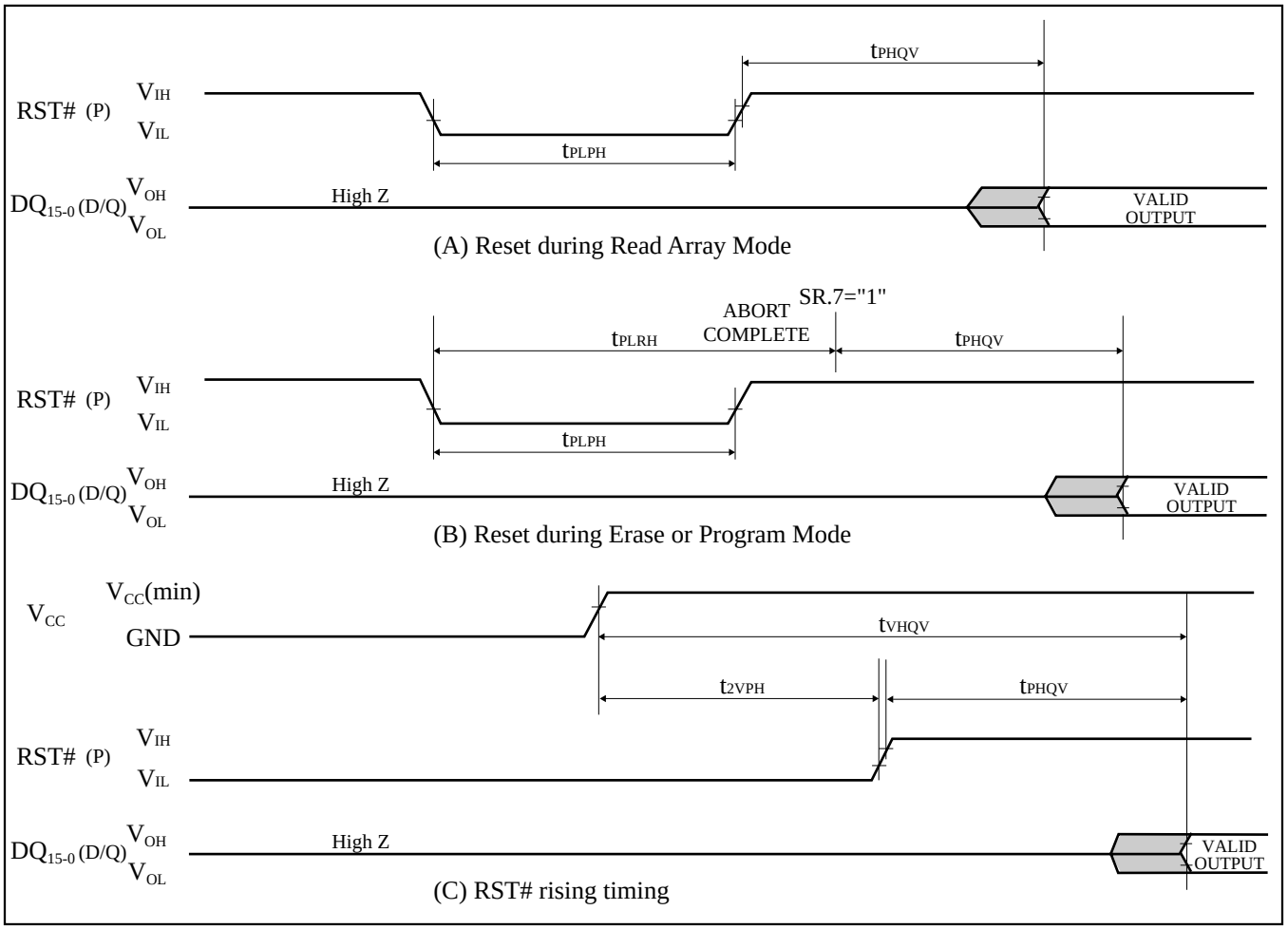


Figure 10. AC Waveform for Reset Operations

Reset AC Specifications (V_{CC}=2.7V-3.3V, T_A=-40°C to +85°C)

Symbol	Parameter	Notes	Min.	Max.	Unit
t_{PLPH}	RST# Low to Reset during Read (RST# should be low during power-up.)	1, 2, 3	100		ns
t_{PLRH}	RST# Low to Reset during Erase or Program	1, 3, 4		22	µs
t_{2VPH}	V_{CC} 2.7V to RST# High	1, 3, 5	100		ns
t_{VHQV}	V_{CC} 2.7V to Output Delay	3		1	ms

NOTES:
1. A reset time, t_{PHQV}, is required from the later of SR.7 (RY/BY#) going "1" (High Z) or RST# going high until outputs are valid. Refer to AC Characteristics - Read-Only Operations for t_{PHQV}.
2. t_{PLPH} is <100ns the device may still reset but this is not guaranteed.
3. Sampled, not 100% tested.
4. If RST# asserted while a block erase, full chip erase, (page buffer) program or OTP program operation is not executing, the reset will complete within 100ns.
5. When the device power-up, holding RST# low minimum 100ns is required after V_{CC} has been in predefined range and also has been in stable there.

1.2.7 Block Erase, Full Chip Erase, (Page Buffer) Program and OTP Program Performance(3)

V_{CC}=2.7V-3.3V, T_A=-40°C to +85°C

Symbol	Parameter	Notes	Page Buffer Command is Used or not Used	WP#/ACC=V_{IL} or V_{IH} (In System)			WP#/ACC=V_{ACCH} (In Manufacturing)			Unit
				Min.	Typ.(1)	Max.(2)	Min.	Typ.(1)	Max.(2)	
t_{WPB}	4-Kword Parameter Block Program Time	2	Not Used		0.05	0.3		0.04	0.12	s
		2	Used		0.03	0.12		0.02	0.06	s
t_{WMB}	32-Kword Main Block Program Time	2	Not Used		0.38	2.4		0.31	1.0	s
		2	Used		0.24	1.0		0.17	0.5	s
t_{WHQV1}/ t_{EHQV1}	Word Program Time	2	Not Used		11	200		9	185	µs
		2	Used		7	100		5	90	µs
t_{WHOV1}/ t_{EHOV1}	OTP Program Time	2	Not Used		36	400		27	185	µs
t_{WHQV2}/ t_{EHQV2}	4-Kword Parameter Block Erase Time	2	-		0.5	4		0.4	4	s
t_{WHQV3}/ t_{EHQV3}	32-Kword Main Block Erase Time	2	-		0.9	5		0.8	5	s
	Full Chip Erase Time	2			240	1400		200	1400	s
t_{WHRH1}/ t_{EHRH1}	(Page Buffer) Program Suspend Latency Time to Read	4	-		5	10		5	10	µs
t_{WHRH2}/ t_{EHRH2}	Block Erase Suspend Latency Time to Read	4	-		5	20		5	20	µs
t_{ERES}	Latency Time from Block Erase Resume Command to Block Erase Suspend Command	5	-	500			500			µs

NOTES:
1. Typical values measured at V_{CC}=3.0V, WP#/ACC=3.0V or 9.5V, and T_A=+25°C. Assumes corresponding lock bits are not set. Subject to change based on device characterization.
2. Excludes external system-level overhead.
3. Sampled, but not 100% tested.
4. A latency time is required from writing suspend command (WE# or CE# going high) until SR.7 going "1" or RY/BY# going High Z.
5. If the interval time from a Block Erase Resume command to a subsequent Block Erase Suspend command is shorter than t_{ERES} and its sequence is repeated, the block erase operation may not be finished.

A-1 RECOMMENDED OPERATING CONDITIONS

A-1.1 At Device Power-Up

AC timing illustrated in Figure A-1 is recommended for the supply voltages and the control signals at device power-up. If the timing in the figure is ignored, the device may not operate correctly.

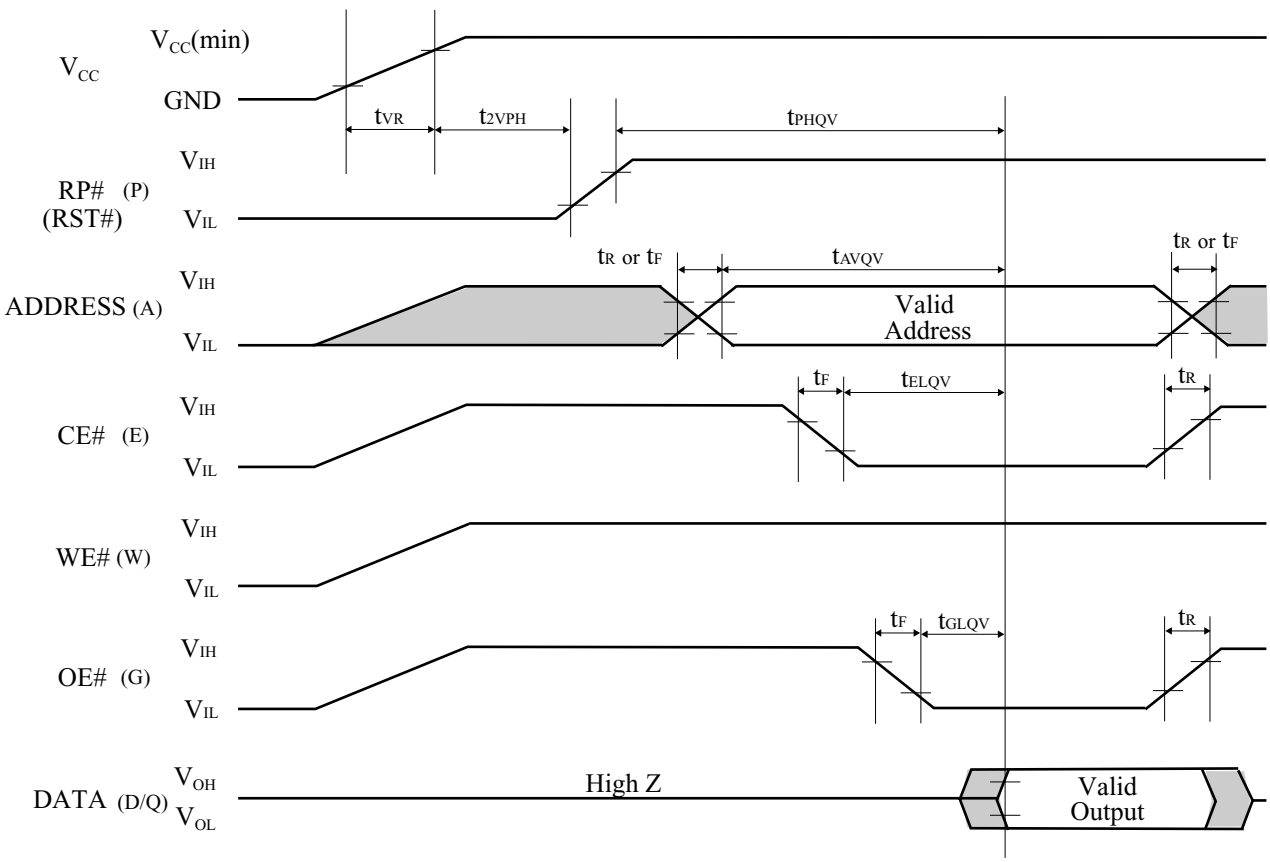


Figure A-1. AC Timing at Device Power-Up

For the AC specifications t_{VR}, t_R, t_F in the figure, refer to the next page. See the "ELECTRICAL SPECIFICATIONS" described in specifications for the supply voltage range, the operating temperature and the AC specifications not shown in the next page.

A-1.1.1 Rise and Fall Time

Symbol	Parameter	Notes	Min.	Max.	Unit
t_{VR}	V_{CC} Rise Time	1	0.5	30000	µs/V
t_R	Input Signal Rise Time	1, 2		1	µs/V
t_F	Input Signal Fall Time	1, 2		1	µs/V

NOTES:
1. Sampled, not 100% tested.
2. This specification is applied for not only the device power-up but also the normal operations.

A-1.2 Glitch Noises

Do not input the glitch noises which are below V_{IH} (Min.) or above V_{IL} (Max.) on address, data, reset, and control signals, as shown in Figure A-2 (b). The acceptable glitch noises are illustrated in Figure A-2 (a).

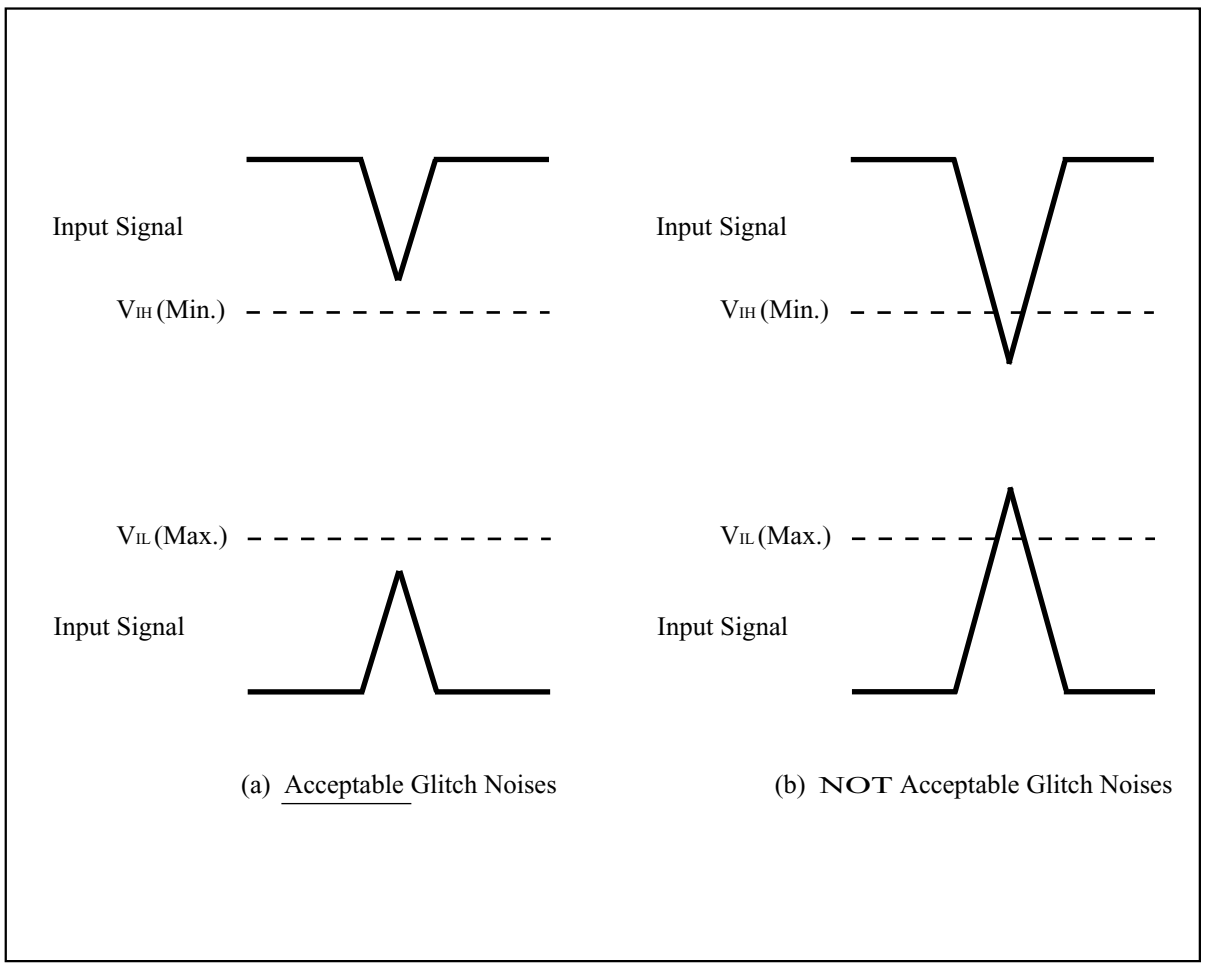


Figure A-2. Waveform for Glitch Noises

See the “DC CHARACTERISTICS“ described in specifications for V_{IH} (Min.) and V_{IL} (Max.).

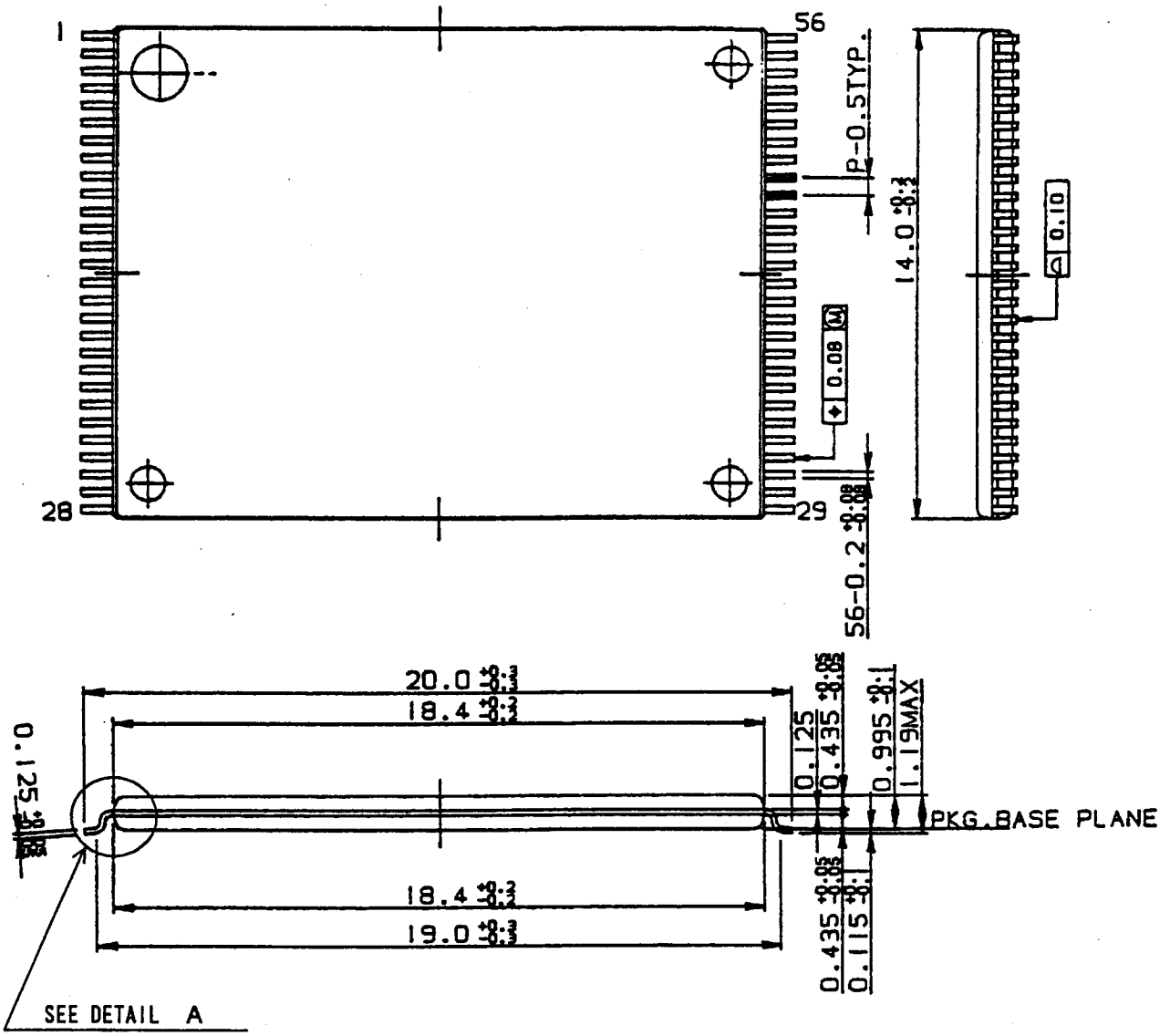
A-2 RELATED DOCUMENT INFORMATION(1)

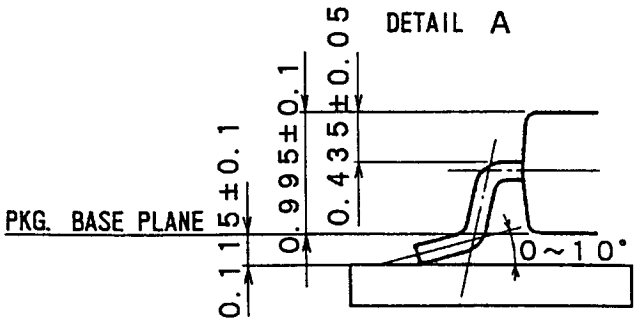
Document No.	Document Name
AP-001-SD-E	Flash Memory Family Software Drivers
AP-006-PT-E	Data Protection Method of SHARP Flash Memory
AP-007-SW-E	RP#, V_{PP} Electric Potential Switching Circuit

NOTE:
1. International customers should contact their local SHARP or distribution sales office.

SHARP

PRELIMINARY





名称 NAME	TSOP56-P-1420	リード仕上 LEAD FINISH	TIN-LEAD PLATING
DRAWING NO.	AA1115	単位 UNIT	mm

備考 プラスチックパッケージ外形寸法は、バリを含まないものとする。
NOTE Plastic body dimensions do not include burr of resin.

SPECIFICATIONS ARE SUBJECT TO CHANGE WITHOUT NOTICE.

Suggested applications (if any) are for standard use; See Important Restrictions for limitations on special applications. See Limited Warranty for SHARP's product warranty. The Limited Warranty is in lieu, and exclusive of, all other warranties, express or implied. ALL EXPRESS AND IMPLIED WARRANTIES, INCLUDING THE WARRANTIES OF MERCHANTABILITY, FITNESS FOR USE AND FITNESS FOR A PARTICULAR PURPOSE, ARE SPECIFICALLY EXCLUDED. In no event will SHARP be liable, or in any way responsible, for any incidental or consequential economic or property damage.

SHARP®

NORTH AMERICA

SHARP Microelectronics of the Americas
5700 NW Pacific Rim Blvd.
Camas, WA 98607, U.S.A.
Phone: (1) 360-834-2500
Fax: (1) 360-834-8903
Fast Info: (1) 800-833-9437
www.sharpsma.com

EUROPE

SHARP Microelectronics Europe
Division of Sharp Electronics (Europe) GmbH
Sonninstrasse 3
20097 Hamburg, Germany
Phone: (49) 40-2376-2286
Fax: (49) 40-2376-2232
www.sharpsme.com

JAPAN

SHARP Corporation
Electronic Components & Devices
22-22 Nagaike-cho, Abeno-Ku
Osaka 545-8522, Japan
Phone: (81) 6-6621-1221
Fax: (81) 6117-725300/6117-725301
www.sharp-world.com

TAIWAN

SHARP Electronic Components
(Taiwan) Corporation
8F-A, No. 16, Sec. 4, Nanking E. Rd.
Taipei, Taiwan, Republic of China
Phone: (886) 2-2577-7341
Fax: (886) 2-2577-7326/2-2577-7328

SINGAPORE

SHARP Electronics (Singapore) PTE., Ltd.
438A, Alexandra Road, #05-01/02
Alexandra Technopark,
Singapore 119967
Phone: (65) 271-3566
Fax: (65) 271-3855

KOREA

SHARP Electronic Components
(Korea) Corporation
RM 501 Geosung B/D, 541
Dohwa-dong, Mapo-ku
Seoul 121-701, Korea
Phone: (82) 2-711-5813 ~ 8
Fax: (82) 2-711-5819

CHINA

SHARP Microelectronics of China
(Shanghai) Co., Ltd.
28 Xin Jin Qiao Road King Tower 16F
Pudong Shanghai, 201206 P.R. China
Phone: (86) 21-5854-7710/21-5834-6056
Fax: (86) 21-5854-4340/21-5834-6057
Head Office:
No. 360, Bashen Road,
Xin Development Bldg. 22
Waigaoqiao Free Trade Zone Shanghai
200131 P.R. China
Email: smc@china.global.sharp.co.jp

HONG KONG

SHARP-ROXY (Hong Kong) Ltd.
3rd Business Division,
17/F, Admiralty Centre, Tower 1
18 Harcourt Road, Hong Kong
Phone: (852) 28229311
Fax: (852) 28660779
www.sharp.com.hk
Shenzhen Representative Office:
Room 13B1, Tower C,
Electronics Science & Technology Building
Shen Nan Zhong Road
Shenzhen, P.R. China
Phone: (86) 755-3273731
Fax: (86) 755-3273735